

<b>Notice of References Cited</b>	Application/Control No. 09/818,193		Applicant(s)/Patent Under Reexamination CHUNG ET AL.	
	Examiner George Fourson		Art Unit 2823	Page 1 of 3

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	Examiner George Fourson	Art Unit 2823	Page 2 of 3

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	Examiner George Fourson	Art Unit 2823	Page 3 of 3

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